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S27 wherein said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first substrate, and

wherein said at least one thin film transistor of the active matrix circuit has at least one lightly doped drain between a channel region and a drain region thereof.

N2 17. (Amended) An electric device comprising:

a first substrate having an insulating surface;

a plurality of thin film transistors formed on the insulating surface, said plurality of thin film transistors being formed from a common semiconductor film formed on said insulating surface;

a second substrate facing said first substrate with a gap therebetween, said first substrate having an extended portion which extends beyond at least one side edge of the second substrate; and

at least one single crystalline semiconductor integrated circuit chip formed on the insulating surface wherein said semiconductor integrated circuit chip is at least one of a memory, an input port, a correction memory and a CPU,

wherein at least one of the thin film transistors is provided as an active matrix circuit, at least another one of the thin film transistors is provided as at least one driving circuit for driving the active matrix circuit and the semiconductor integrated circuit chip is provided as a control circuit for controlling the driving circuit, and wherein said common semiconductor film is formed by crystallizing a semiconductor film comprising amorphous silicon deposited on said insulating surface.

N3 18. (Amended) The device of claim 17 wherein the first substrate comprises a glass substrate.

N4 46. (Amended) The device according to claim 17 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said first substrate.

25 51. (Amended) An electric device comprising:
a first insulating substrate;
an active matrix circuit including at least one thin film transistor formed over said first insulating substrate;
a driving circuit including at least another one thin film transistor for driving the active matrix circuit formed over said first insulating substrate;
a second substrate facing said first insulating substrate with a gap therebetween, said first insulating substrate having an extended portion which extends beyond at least one side edge of the second substrate; and
at least one semiconductor integrated circuit chip disposed over said first insulating substrate and operationally connected with the driving circuit wherein said integrated circuit chip is at least one of a memory, an input port, a correction memory and a CPU,
wherein said at least one thin film transistor and said at least another one thin film transistor are formed from a common semiconductor film formed over the first insulating substrate, and
wherein said at least one thin film transistor of the active matrix circuit has at least one lightly doped drain between a channel region and a drain region thereof.

26 54. (Amended) The device of claim 51 wherein the first insulating substrate comprises a glass substrate.

55. (Amended) The electric device according to claim 51 wherein said semiconductor integrated circuit chip is connected to a wiring comprising indium tin oxide formed over said first insulating substrate.